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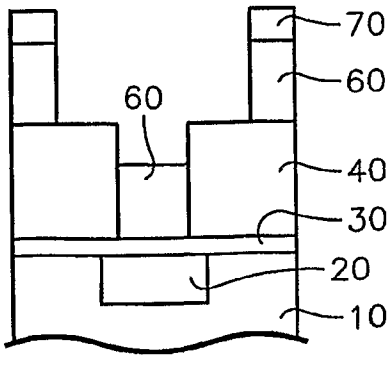
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(54) Title: ORGANIC BARC ETCH PROCESS CAPABLE OF USE IN THE FORMATION OF LOW K DUAL DAMASCENE INTEGRATED CIRCUITS



(57) Abstract: In some implementations, a method is provided in a plasma reactor for etching a trench in an organic planarization layer of a resist structure comprising a photoresist mask structure over a hardmask masking the organic planarization layer. This may include introducing into the plasma reactor an etchant gas chemistry including N_2, H_2, and O_2 and etching a masked organic planarization layer using a plasma formed from the etchant gas chemistry. This may include etching through the planarization layer to form a trench with a single etch step.